GRINDING METHOD FOR GRINDING BACK-SURFACE OF SEMICONDUCTOR WAFER AND GRINDING APPARATUS FOR GRINDING BACK-SURFACE OF SEMICONDUCTOR WAFER USED IN SAME

ABSTRACT OF THE DISCLOSURE

A grinding method for grinding a back surface of a semiconductor wafer that performs infeed grinding of a back surface of a wafer laminated body, the method, during the grinding of the back surface of the wafer laminated body, having: measuring respectively a thickness of an outer peripheral portion and an inner peripheral portion of the wafer laminated body; calculating a thickness difference between the thickness of the outer portion and the thickness the inner portion; and tilting an axis of a grinding wheel by a predetermined angle in an arbitrary direction so as to reduce the calculated thickness difference.

Fig. 5A